

**b. Amendments to the Specification**

**Please rewrite the paragraph between page 16, line 30, and page 17, line 2, as follows:**

[[.]] The MOMBE growth is stopped when n-type InP collector layer 98' has a thickness of 1,500 Å - 2,500 Å. After the MOMBE growth, a wash with the same aqueous HF solution removes the SiO<sub>2</sub> mask thereby producing structure 74' of Figure 10. The resulting collector layer 98' has a limited lateral extent, which produces a nontrivial cross-sectional profile.